

256Kx16 4Mb DRAM WITH EDO PAGE MODE

JANUARY 2013

FEATURES

- TTL compatible inputs and outputs; tri-state I/O
- Refresh Interval: 512 cycles/8 ms
- Refresh Mode : $\overline{\text{RAS}}$ -Only, $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ (CBR), and Hidden
- JEDEC standard pinout
- Single power supply:
5V \pm 10% (IS41C16256C)
3.3V \pm 10% (IS41LV16256C)
- Byte Write and Byte Read operation via two $\overline{\text{CAS}}$
- Industrial Temperature Range -40°C to +85°C

DESCRIPTION

The IS41C16256C and IS41LV16256C are 262,144 x 16-bit high-performance CMOS Dynamic Random Access Memories. Both products offer accelerated cycle access EDO Page Mode. EDO Page Mode allows 512 random accesses within a single row with access cycle time as short as 14ns per 16-bit word. It is asynchronous, as it does not require a clock signal input to synchronize commands and I/O.

These features make the IS41C/LV16256C ideally suited for high band-width graphics, digital signal processing, high-performance computing systems, and peripheral applications that run without a clock to synchronize with the DRAM.

The IS41C/LV16256C is packaged in 40-pin TSOP (Type II).

KEY TIMING PARAMETERS

| Parameter | -35 | Unit |
|---|-----|------|
| Max. $\overline{\text{RAS}}$ Access Time (t_{RAC}) | 35 | ns |
| Max. $\overline{\text{CAS}}$ Access Time (t_{CAC}) | 13 | ns |
| Max. Column Address Access Time (t_{AA}) | 18 | ns |
| Min. EDO Page Mode Cycle Time (t_{PC}) | 14 | ns |
| Min. Read/Write Cycle Time (t_{RC}) | 60 | ns |

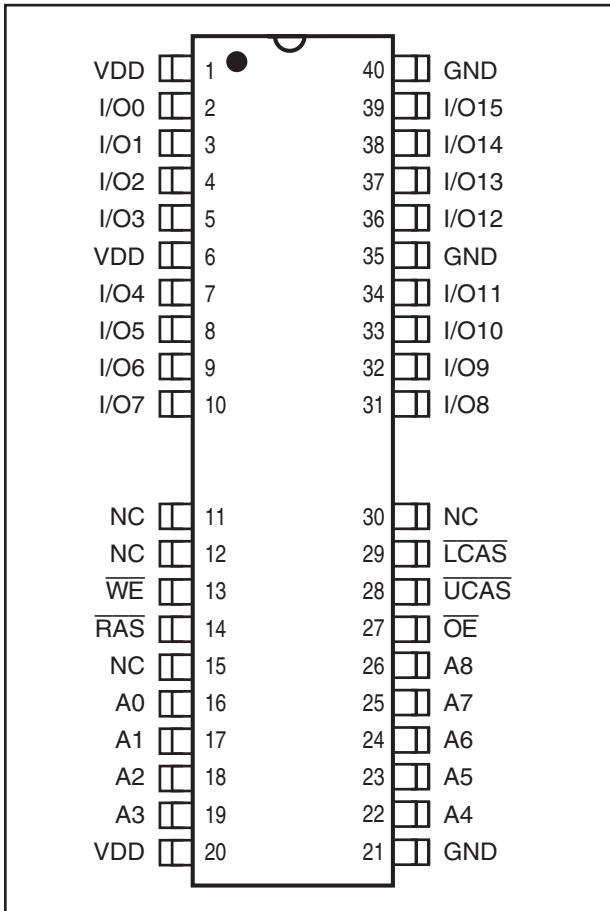
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PIN CONFIGURATIONS

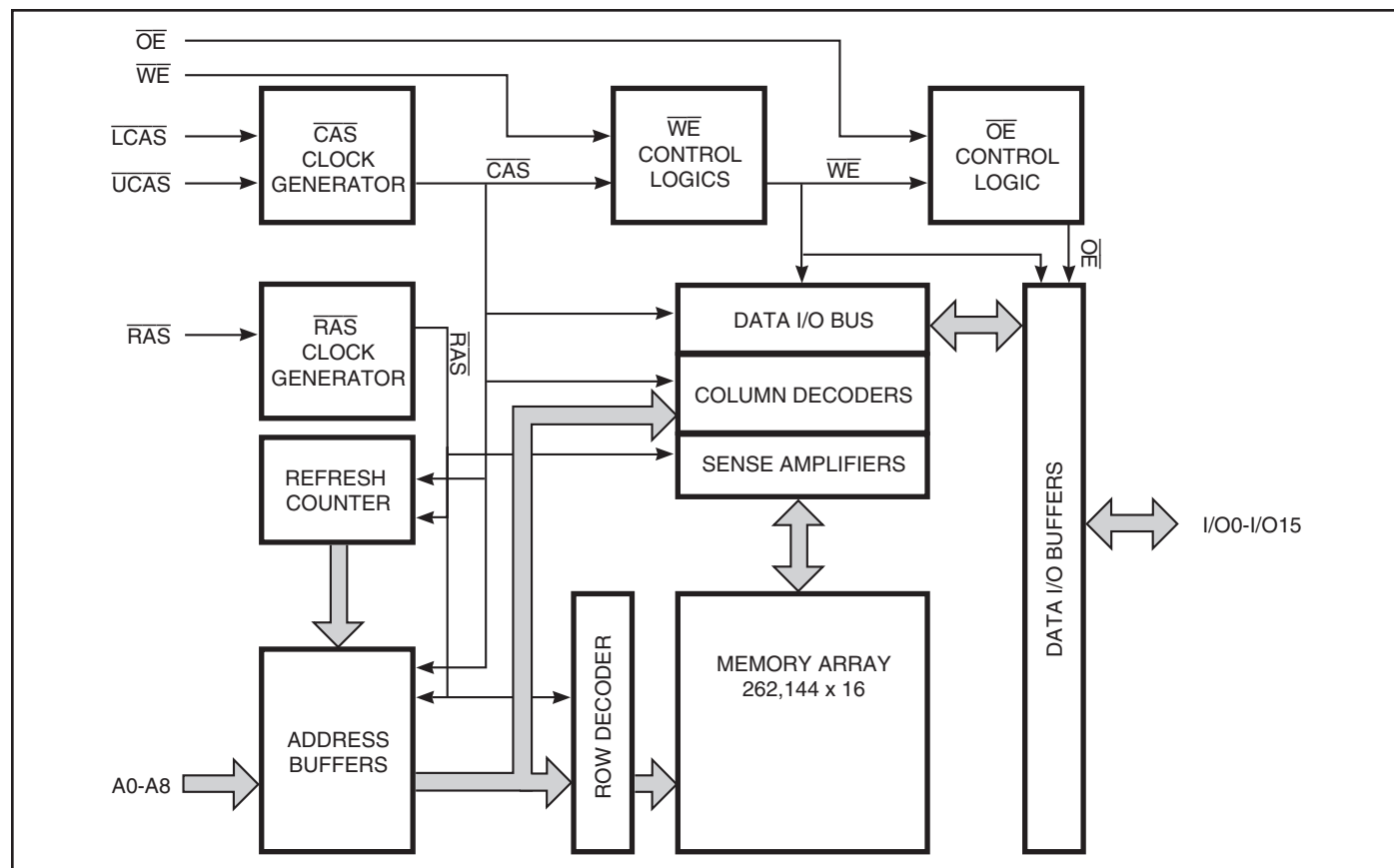
40-Pin TSOP (Type II)



PIN DESCRIPTIONS

| | |
|---------|-----------------------------|
| A0-A8 | Address Inputs |
| I/O0-15 | Data Inputs/Outputs |
| WE | Write Enable |
| OE | Output Enable |
| RAS | Row Address Strobe |
| UCAS | Upper Column Address Strobe |
| LCAS | Lower Column Address Strobe |
| VDD | Power |
| GND | Ground |
| NC | No Connection |

FUNCTIONAL BLOCK DIAGRAM



TRUTH TABLE⁽⁵⁾

| Function | $\overline{\text{RAS}}$ | $\overline{\text{LCAS}}$ | $\overline{\text{UCAS}}$ | $\overline{\text{WE}}$ | $\overline{\text{OE}}$ | Address $t_{\text{R}}/t_{\text{C}}$ | I/O |
|---|-------------------------|--------------------------|--------------------------|------------------------|------------------------|-------------------------------------|--|
| Standby | H | X | X | X | X | X | High-Z |
| Read: Word | L | L | L | H | L | ROW/COL | DOUT |
| Read: Lower Byte | L | L | H | H | L | ROW/COL | Lower Byte, DOUT Upper Byte, High-Z |
| Read: Upper Byte | L | H | L | H | L | ROW/COL | Lower Byte, High-Z Upper Byte, DOUT |
| Write: Word (Early Write) | L | L | L | L | X | ROW/COL | DIN |
| Write: Lower Byte (Early Write) | L | L | H | L | X | ROW/COL | Lower Byte, DIN Upper Byte, High-Z |
| Write: Upper Byte (Early Write) | L | H | L | L | X | ROW/COL | Lower Byte, High-Z Upper Byte, DIN |
| Read-Write ^(1,2) | L | L | L | H→L | L→H | ROW/COL | DOUT, DIN |
| EDO Page-Mode Read ⁽²⁾ | 1st Cycle: | L | H→L | H→L | H | L | ROW/COL DOUT |
| | 2nd Cycle: | L | H→L | H→L | H | L | NA/COL DOUT |
| | Any Cycle: | L | L→H | L→H | H | L | NA/NA DOUT |
| EDO Page-Mode Write ⁽¹⁾ | 1st Cycle: | L | H→L | H→L | L | X | ROW/COL DIN |
| | 2nd Cycle: | L | H→L | H→L | L | X | NA/COL DIN |
| EDO Page-Mode Read-Write ^(1,2) | 1st Cycle: | L | H→L | H→L | H→L | L→H | ROW/COL DOUT, DIN |
| | 2nd Cycle: | L | H→L | H→L | H→L | L→H | NA/COL DOUT, DIN |
| Hidden Refresh | Read ⁽²⁾ | L→H→L | L | L | H | L | ROW/COL DOUT |
| | Write ^(1,3) | L→H→L | L | L | L | X | ROW/COL DOUT |
| $\overline{\text{RAS}}$ -Only Refresh | | L | H | H | X | X | ROW/NA High-Z |
| CBR Refresh ⁽⁴⁾ | | H→L | L | L | H | X | X High-Z |

Notes:

1. These WRITE cycles may also be BYTE WRITE cycles (either $\overline{\text{LCAS}}$ or $\overline{\text{UCAS}}$ active).
2. These READ cycles may also be BYTE READ cycles (either $\overline{\text{LCAS}}$ or $\overline{\text{UCAS}}$ active).
3. Early write only.
4. At least one of the two $\overline{\text{CAS}}$ signals must be active ($\overline{\text{LCAS}}$ or $\overline{\text{UCAS}}$).
5. Commands valid only after proper initialization.

Functional Description

The IS41C/LV16256C is a CMOS DRAM optimized for high-speed bandwidth, low power applications. During READ or WRITE cycles, each bit is uniquely addressed through the 18 address bits. These are entered nine bits (A0-A8) at a time. The row address is latched by the Row Address Strobe ($\overline{\text{RAS}}$). The column address is latched by the Column Address Strobe ($\overline{\text{CAS}}$). $\overline{\text{RAS}}$ is used to latch the first nine bits and $\overline{\text{CAS}}$ is used the latter nine bits.

The IS41C/LV16256C has two $\overline{\text{CAS}}$ controls, $\overline{\text{LCAS}}$ and $\overline{\text{UCAS}}$. The $\overline{\text{LCAS}}$ and $\overline{\text{UCAS}}$ inputs internally generate a $\overline{\text{CAS}}$ signal functioning in an identical manner to the single $\overline{\text{CAS}}$ input on the other 256K x 16 DRAMs. The key difference is that each $\overline{\text{CAS}}$ controls its corresponding I/O tristate logic (in conjunction with $\overline{\text{OE}}$ and $\overline{\text{WE}}$ and $\overline{\text{RAS}}$). $\overline{\text{LCAS}}$ controls I/O0 through I/O7 and $\overline{\text{UCAS}}$ controls I/O8 through I/O15.

The IS41C/LV16256C $\overline{\text{CAS}}$ function is determined by the first $\overline{\text{CAS}}$ ($\overline{\text{LCAS}}$ or $\overline{\text{UCAS}}$) transitioning LOW and the last transitioning back HIGH. The two $\overline{\text{CAS}}$ controls give the IS41C/LV16256C both BYTE READ and BYTE WRITE cycle capabilities.

Memory Cycle

A memory cycle is initiated by bring $\overline{\text{RAS}}$ LOW and it is terminated by returning both $\overline{\text{RAS}}$ and $\overline{\text{CAS}}$ HIGH. To ensure proper device operation and data integrity any memory cycle, once initiated, must not be ended or aborted before the minimum t_{RAS} time has expired. A new cycle must not be initiated until the minimum precharge time t_{RP} , t_{CP} has elapsed.

Read Cycle

A read cycle is initiated by the falling edge of $\overline{\text{CAS}}$ or $\overline{\text{OE}}$, whichever occurs last, while holding $\overline{\text{WE}}$ HIGH. The column address must be held for a minimum time specified by t_{AR} . Data Out becomes valid only when t_{RAC} , t_{AA} , t_{CAC} and t_{OEA} are all satisfied. As a result, the access time is dependent on the timing relationships between these parameters.

Write Cycle

A write cycle is initiated by the falling edge of $\overline{\text{CAS}}$ and $\overline{\text{WE}}$, whichever occurs last. The input data must be valid at or before the falling edge of $\overline{\text{CAS}}$ or $\overline{\text{WE}}$, whichever occurs last.

Refresh Cycle

To retain data, 512 refresh cycles are required in each 8 ms period. There are two ways to refresh the memory.

1. By clocking each of the 512 row addresses (A0 through A8) with $\overline{\text{RAS}}$ at least once every 8 ms. Any read, write, read-modify-write or $\overline{\text{RAS}}$ -only cycle refreshes the addressed row.
2. Using a $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ refresh cycle. $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ refresh is activated by the falling edge of $\overline{\text{RAS}}$, while holding $\overline{\text{CAS}}$ LOW. In $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ refresh cycle, an internal 9-bit counter provides the row addresses and the external address inputs are ignored. $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ is a refresh-only mode and no data access or device selection is allowed. Thus, the output remains in the High-Z state during the cycle.

Extended Data Out Page Mode

EDO page mode operation permits all 512 columns within a selected row to be randomly accessed at a high data rate.

In EDO page mode read cycle, the data-out is held to the next $\overline{\text{CAS}}$ cycle's falling edge, instead of the rising edge. For this reason, the valid data output time in EDO page mode is extended compared with the fast page mode. In the fast page mode, the valid data output time becomes shorter as the $\overline{\text{CAS}}$ cycle time becomes shorter. Therefore, in EDO page mode, the timing margin in read cycle is larger than that of the fast page mode even if the $\overline{\text{CAS}}$ cycle time becomes shorter.

In EDO page mode, due to the extended data function, the $\overline{\text{CAS}}$ cycle time can be shorter than in the fast page mode if the timing margin is the same.

The EDO page mode allows both read and write operations during one $\overline{\text{RAS}}$ cycle, but the performance is equivalent to that of the fast page mode in that case.

Power-On

During Power-on, $\overline{\text{RAS}}$, $\overline{\text{CAS}}$, $\overline{\text{UCAS}}$, $\overline{\text{LCAS}}$, and $\overline{\text{WE}}$ must all track with V_{DD} (HIGH) to avoid current surges, and allow initialization to continue. An initial pause of 200 μs is required followed by a minimum of eight initialization cycles (any combination of cycles containing a $\overline{\text{RAS}}$ signal).

ABSOLUTE MAXIMUM RATINGS⁽¹⁾

| Symbol | Parameters | Rating | Unit |
|------------------|------------------------------------|-------------|----------------|
| V _T | Voltage on Any Pin Relative to GND | 5V | -1.0 to +7.0 V |
| | | 3.3V | -0.5 to +4.6 V |
| V _{DD} | Supply Voltage | 5V | -1.0 to +7.0 V |
| | | 3.3V | -0.5 to +4.6 V |
| I _{OUT} | Output Current | 50 | mA |
| P _D | Power Dissipation | 1 | W |
| T _A | Operation Temperature | -40 to +85 | °C |
| T _{STG} | Storage Temperature | -55 to +125 | °C |

Note:

1. Stress greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

RECOMMENDED OPERATING CONDITIONS (Voltages are referenced to GND.)

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|-----------------|---------------------------|--|------|------|------|-------------------------|
| V _{DD} | Supply Voltage | | 5V | 4.5 | 5.0 | 5.5 V |
| | | | 3.3V | 3.0 | 3.3 | 3.6 V |
| V _{IH} | Input High Voltage | | 5V | 2.4 | — | V _{DD} + 1.0 V |
| | | | 3.3V | 2.0 | — | V _{DD} + 0.3 V |
| V _{IL} | Input Low Voltage | | 5V | -1.0 | — | 0.8 V |
| | | | 3.3V | -0.3 | — | 0.8 V |
| I _{IL} | Input Leakage Current | Any input 0V ≤ V _{IN} ≤ V _{DD} Other inputs not under test = 0V | -5 | | 5 | μA |
| I _{IO} | Output Leakage Current | Output is disabled (Hi-Z) 0V ≤ V _{OUT} ≤ V _{DD} | -5 | | 5 | μA |
| V _{OH} | Output High Voltage Level | I _{OH} = -5.0 mA | 5V | 2.4 | — | V |
| | | I _{OH} = -2.0 mA | 3.3V | 2.4 | — | V |
| V _{OL} | Output Low Voltage Level | I _{OL} = +4.2 mA | 5V | — | 0.4 | V |
| | | I _{OL} = +2.0 mA | 3.3V | — | 0.4 | V |

CAPACITANCE^(1,2)

| Symbol | Parameter | Max. | Unit |
|------------------|--|------|------|
| C _{IN1} | Input Capacitance: A0-A8 | 5 | pF |
| C _{IN2} | Input Capacitance: $\overline{\text{RAS}}$, $\overline{\text{UCAS}}$, $\overline{\text{LCAS}}$, $\overline{\text{WE}}$, $\overline{\text{OE}}$ | 7 | pF |
| C _{IO} | Data Input/Output Capacitance: I/O0-I/O15 | 7 | pF |

Notes:

1. Tested initially and after any design or process changes that may affect these parameters.
2. Test conditions: T_A = 25°C, f = 1 MHz,

ELECTRICAL CHARACTERISTICS⁽¹⁾

(Recommended Operation Conditions unless otherwise noted.)

| Symbol | Parameter | Test Condition | V _{DD} | Max. | Unit |
|------------------|--|--|-----------------|------|------|
| I _{DD1} | Stand-by Current: TTL | $\overline{\text{RAS}}, \overline{\text{LCAS}}, \overline{\text{UCAS}} \geq V_{IH}$ | 5V | 2 | mA |
| | | | 3.3V | 2 | mA |
| I _{DD2} | Stand-by Current: CMOS | $\overline{\text{RAS}}, \overline{\text{LCAS}}, \overline{\text{UCAS}} \geq V_{DD} - 0.2V$ | 5V | 1 | mA |
| | | | 3.3V | 1 | mA |
| I _{DD3} | Operating Current: Random Read/Write ^(2,3,4) Average Power Supply Current | $\overline{\text{RAS}}, \overline{\text{LCAS}}, \overline{\text{UCAS}},$ Address Cycling, $t_{RC} = t_{RC} (\text{min.})$ | 5V | 150 | mA |
| | | | 3.3V | 90 | mA |
| I _{DD4} | Operating Current: EDO Page Mode ^(2,3,4) Average Power Supply Current | $\overline{\text{RAS}} = V_{IL}, \overline{\text{LCAS}}, \overline{\text{UCAS}},$ Cycling $t_{PC} = t_{PC} (\text{min.})$ | 5V | 60 | mA |
| | | | 3.3V | 30 | mA |
| I _{DD5} | Refresh Current: $\overline{\text{RAS}}$ -Only ^(2,3) Average Power Supply Current | $\overline{\text{RAS}}$ Cycling, $\overline{\text{LCAS}}, \overline{\text{UCAS}} \geq V_{IH}$ $t_{RC} = t_{RC} (\text{min.})$ | 5V | 90 | mA |
| | | | 3.3V | 60 | mA |
| I _{DD6} | Refresh Current: CBR ^(2,3,5) Average Power Supply Current | $\overline{\text{RAS}}, \overline{\text{LCAS}}, \overline{\text{UCAS}}$ Cycling $t_{RC} = t_{RC} (\text{min.})$ | 5V | 90 | mA |
| | | | 3.3V | 60 | mA |

Notes:

1. An initial pause of 200 μs is required after power-up followed by eight $\overline{\text{RAS}}$ refresh cycles ($\overline{\text{RAS}}$ -Only or CBR) before proper device operation is assured. The eight $\overline{\text{RAS}}$ cycles wake-up should be repeated any time the t_{REF} refresh requirement is exceeded.
2. Dependent on cycle rates.
3. Specified values are obtained with minimum cycle time and the output open.
4. Column-address is changed once each EDO page cycle.
5. Enables on-chip refresh and address counters.

AC CHARACTERISTICS^(1,2,3,4,5,6)

(Recommended Operating Conditions unless otherwise noted.)

| Symbol | Parameter | -35 | | Units |
|------------------------------------|--|------|------|-------|
| | | Min. | Max. | |
| t _{RC} | Random READ or WRITE Cycle Time | 70 | — | ns |
| t _{RAC} | Access Time from $\overline{\text{RAS}}$ ^(6, 7) | 35 | — | ns |
| t _{CAC} | Access Time from $\overline{\text{CAS}}$ ^(6, 8, 15) | — | 13 | ns |
| t _{AA} | Access Time from Column-Address ⁽⁶⁾ | — | 18 | ns |
| t _{RAS} | $\overline{\text{RAS}}$ Pulse Width | 35 | 10K | ns |
| t _{RP} | $\overline{\text{RAS}}$ Precharge Time | 25 | — | ns |
| t _{CAS} | $\overline{\text{CAS}}$ Pulse Width ⁽²⁶⁾ | 6 | 10K | ns |
| t _{CP} | $\overline{\text{CAS}}$ Precharge Time ^(9, 25) | 6 | — | ns |
| t _{CSH} | $\overline{\text{CAS}}$ Hold Time ⁽²¹⁾ | 35 | — | ns |
| t _{RCD} | $\overline{\text{RAS}}$ to $\overline{\text{CAS}}$ Delay Time ^(10, 20) | 13 | 22 | ns |
| t _{ASR} | Row-Address Setup Time | 0 | — | ns |
| t _{RAH} | Row-Address Hold Time | 6 | — | ns |
| t _{ASC} | Column-Address Setup Time ⁽²⁰⁾ | 0 | — | ns |
| t _{CAH} | Column-Address Hold Time ⁽²⁰⁾ | 6 | — | ns |
| t _{AR} | Column-Address Hold Time (referenced to $\overline{\text{RAS}}$) | 30 | — | ns |
| t _{RAD} | $\overline{\text{RAS}}$ to Column-Address Delay Time ⁽¹¹⁾ | 10 | 20 | ns |
| t _{RAL} | Column-Address to $\overline{\text{RAS}}$ Lead Time | 18 | — | ns |
| t _{RPC} | $\overline{\text{RAS}}$ to $\overline{\text{CAS}}$ Precharge Time | 0 | — | ns |
| t _{RS} | $\overline{\text{RAS}}$ Hold Time ⁽²⁷⁾ | 10 | — | ns |
| t _{RHCP} | $\overline{\text{RAS}}$ Hold Time from $\overline{\text{CAS}}$ Precharge | 35 | — | ns |
| t _{CLZ} | $\overline{\text{CAS}}$ to Output in Low-Z ^(15, 29) | 3 | — | ns |
| t _{CRP} | $\overline{\text{CAS}}$ to $\overline{\text{RAS}}$ Precharge Time ⁽²¹⁾ | 5 | — | ns |
| t _{OD} | Output Disable Time ^(19, 28, 29) | 3 | 15 | ns |
| t _{OE} / t _{OEA} | Output Enable Time ^(15, 16) | 0 | 13 | ns |
| t _{OEHC} | $\overline{\text{OE}}$ HIGH Hold Time from $\overline{\text{CAS}}$ HIGH | 8 | — | ns |
| t _{OEP} | $\overline{\text{OE}}$ HIGH Pulse Width | 8 | — | ns |
| t _{OES} | $\overline{\text{OE}}$ LOW to $\overline{\text{CAS}}$ HIGH Setup Time | 5 | — | ns |
| t _{RCS} | Read Command Setup Time ^(17, 20) | 0 | — | ns |
| t _{RRH} | Read Command Hold Time (referenced to $\overline{\text{RAS}}$) ⁽¹²⁾ | 0 | — | ns |
| t _{RCH} | Read Command Hold Time (referenced to $\overline{\text{CAS}}$) ^(12, 17, 21) | 0 | — | ns |
| t _{WCH} | Write Command Hold Time ^(17, 27) | 5 | — | ns |
| t _{WCR} | Write Command Hold Time (referenced to $\overline{\text{RAS}}$) ⁽¹⁷⁾ | 30 | — | ns |

AC CHARACTERISTICS (Continued)^(1,2,3,4,5,6)

(Recommended Operating Conditions unless otherwise noted.)

| Symbol | Parameter | -35 | | Units |
|-------------|---|------|------|-------|
| | | Min. | Max. | |
| tWP | Write Command Pulse Width ⁽¹⁷⁾ | 5 | — | ns |
| tWPZ | \overline{WE} Pulse Widths to Disable Outputs | 10 | — | ns |
| tRWL | Write Command to \overline{RAS} Lead Time ⁽¹⁷⁾ | 10 | — | ns |
| tcWL | Write Command to \overline{CAS} Lead Time ^(17, 21) | 8 | — | ns |
| twCS | Write Command Setup Time ^(14, 17, 20) | 0 | — | ns |
| tDHR | Data-in Hold Time (referenced to \overline{RAS}) | 30 | — | ns |
| tACH | Column-Address Setup Time to \overline{CAS} Precharge during WRITE Cycle | 15 | — | ns |
| toEH | \overline{OE} Hold Time from \overline{WE} during READ-MODIFY-WRITE cycle ⁽¹⁸⁾ | 8 | — | ns |
| tdS | Data-In Setup Time ^(15, 22) | 0 | — | ns |
| tdH | Data-In Hold Time ^(15, 22) | 6 | — | ns |
| trWC | READ-MODIFY-WRITE Cycle Time | 80 | — | ns |
| trWD | \overline{RAS} to \overline{WE} Delay Time during READ-MODIFY-WRITE Cycle ⁽¹⁴⁾ | 46 | — | ns |
| tcWD | \overline{CAS} to \overline{WE} Delay Time ^(14, 20) | 25 | — | ns |
| tAWD | Column-Address to \overline{WE} Delay Time ⁽¹⁴⁾ | 30 | — | ns |
| tPC | EDO Page Mode READ or WRITE Cycle Time ⁽²⁴⁾ | 14 | — | ns |
| trASP | \overline{RAS} Pulse Width in EDO Page Mode | 35 | 100K | ns |
| tCPA | Access Time from \overline{CAS} Precharge ⁽¹⁵⁾ | — | 20 | ns |
| tPRWC | EDO Page Mode READ-WRITE Cycle Time ⁽²⁴⁾ | 45 | — | ns |
| tCOH / tDOH | Data Output Hold after \overline{CAS} LOW | 5 | — | ns |
| tOFF | Output Buffer Turn-Off Delay from \overline{CAS} or \overline{RAS} ^(13,15,19, 29) | 3 | 10 | ns |
| tWHZ | Output Disable Delay from \overline{WE} | 3 | 10 | ns |
| tCLCH | Last \overline{CAS} going LOW to First \overline{CAS} returning HIGH ⁽²³⁾ | 10 | — | ns |
| tCSR | \overline{CAS} Setup Time (CBR REFRESH) ^(30, 20) | 8 | — | ns |
| tCHR | \overline{CAS} Hold Time (CBR REFRESH) ^(30, 21) | 8 | — | ns |
| tORD | \overline{OE} Setup Time prior to \overline{RAS} during HIDDEN REFRESH Cycle | 0 | — | ns |
| tWRP | \overline{WE} Setup Time (CBR Refresh) | 5 | — | ns |
| tWRH | \overline{WE} Hold Time (CBR Refresh) | 8 | — | ns |
| tREF | Refresh Period (512 Cycles) | — | 8 | ns |
| tr | Transition Time (Rise or Fall) ^(2, 3) | 2 | 50 | ns |

AC TEST CONDITIONS

Output load: Two TTL Loads and 100 pF ($V_{DD} = 5.0V \pm 10\%$)
One TTL Load and 50 pF ($V_{DD} = 3.3V \pm 10\%$)

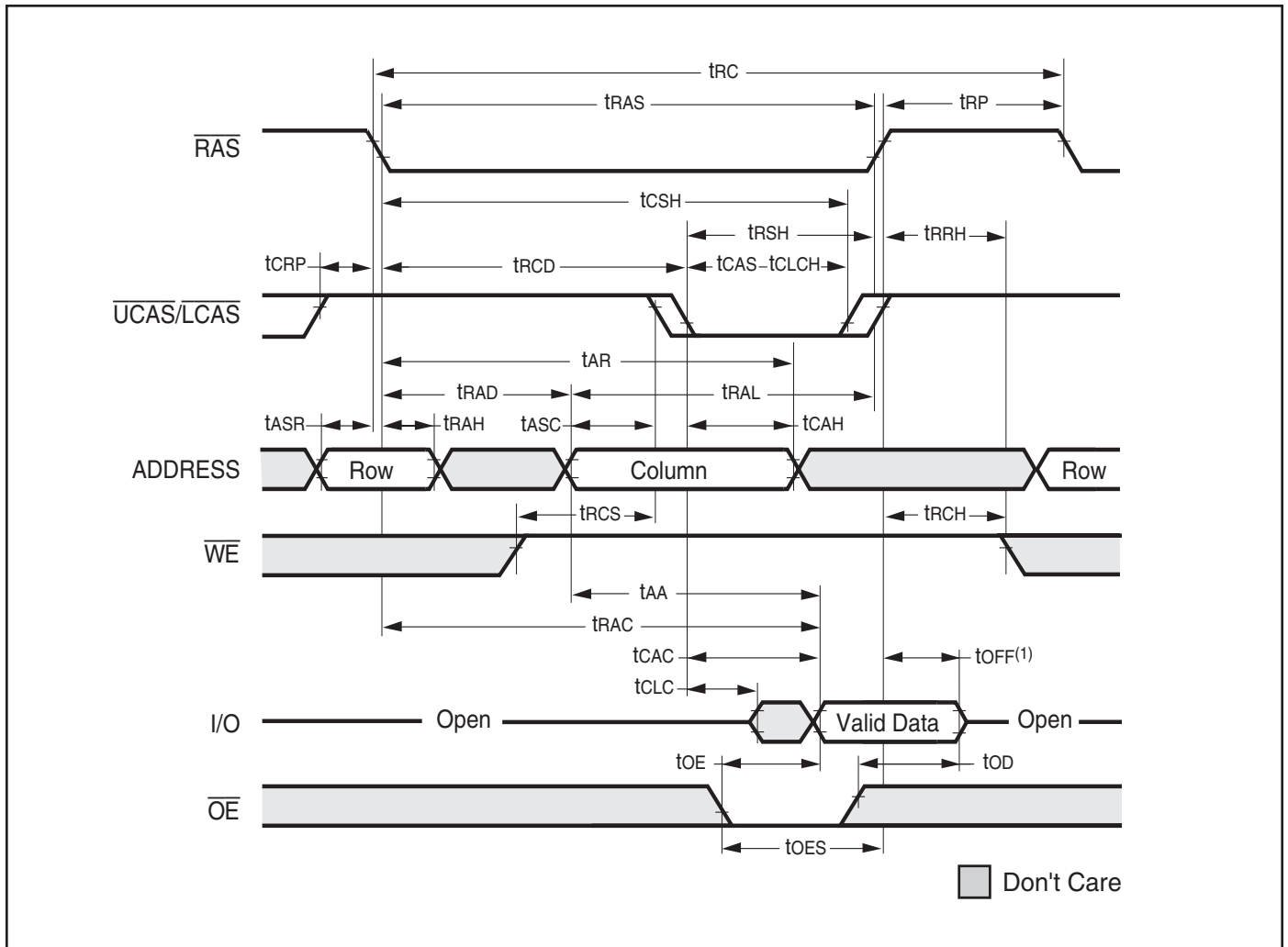
Input timing reference levels: $V_{IH} = 2.4V$, $V_{IL} = 0.8V$ ($V_{DD} = 5.0V \pm 10\%$);
 $V_{IH} = 2.0V$, $V_{IL} = 0.8V$ ($V_{DD} = 3.3V \pm 10\%$)

Output timing reference levels: $V_{OH} = 2.4V$, $V_{OL} = 0.4V$ ($V_{DD} = 5V \pm 10\%$, $3.3V \pm 10\%$)

Notes:

1. An initial pause of 200 μs is required after power-up followed by eight \overline{RAS} refresh cycle (\overline{RAS} -Only or CBR) before proper device operation is assured. The eight \overline{RAS} cycles wake-up should be repeated any time the t_{REF} refresh requirement is exceeded.
2. V_{IH} (MIN) and V_{IL} (MAX) are reference levels for measuring timing of input signals. Transition times, are measured between V_{IH} and V_{IL} (or between V_{IL} and V_{IH}) and assume to be 1 ns for all inputs.
3. In addition to meeting the transition rate specification, all input signals must transit between V_{IH} and V_{IL} (or between V_{IL} and V_{IH}) in a monotonic manner.
4. If \overline{CAS} and $\overline{RAS} = V_{IH}$, data output is High-Z.
5. If $\overline{CAS} = V_{IL}$, data output may contain data from the last valid READ cycle.
6. Measured with a load equivalent to one TTL gate and 50 pF.
7. Assumes that $tr_{CD} \leq tr_{CD} (MAX)$. If tr_{CD} is greater than the maximum recommended value shown in this table, tr_{AC} will increase by the amount that tr_{CD} exceeds the value shown.
8. Assumes that $tr_{CD} \geq tr_{CD} (MAX)$.
9. If \overline{CAS} is LOW at the falling edge of \overline{RAS} , data out will be maintained from the previous cycle. To initiate a new cycle and clear the data output buffer, \overline{CAS} and \overline{RAS} must be pulsed for t_{CP} .
10. Operation with the $tr_{CD} (MAX)$ limit ensures that $tr_{AC} (MAX)$ can be met. $tr_{CD} (MAX)$ is specified as a reference point only; if tr_{CD} is greater than the specified $tr_{CD} (MAX)$ limit, access time is controlled exclusively by t_{CAC} .
11. Operation within the $tr_{AD} (MAX)$ limit ensures that $tr_{CD} (MAX)$ can be met. $tr_{AD} (MAX)$ is specified as a reference point only; if tr_{AD} is greater than the specified $tr_{AD} (MAX)$ limit, access time is controlled exclusively by t_{AA} .
12. Either tr_{CH} or tr_{RH} must be satisfied for a READ cycle.
13. $t_{OFF} (MAX)$ defines the time at which the output achieves the open circuit condition; it is not a reference to V_{OH} or V_{OL} .
14. tw_{CS} , tr_{WD} , t_{AWD} and tc_{WD} are restrictive operating parameters in LATE WRITE and READ-MODIFY-WRITE cycle only. If $tw_{CS} \geq tw_{CS} (MIN)$, the cycle is an EARLY WRITE cycle and the data output will remain open circuit throughout the entire cycle. If $tr_{WD} \geq tr_{WD} (MIN)$, $t_{AWD} \geq t_{AWD} (MIN)$ and $tc_{WD} \geq tc_{WD} (MIN)$, the cycle is a READ-WRITE cycle and the data output will contain data read from the selected cell. If neither of the above conditions is met, the state of I/O (at access time and until \overline{CAS} and \overline{RAS} or \overline{OE} go back to V_{IH}) is indeterminate. \overline{OE} held HIGH and \overline{WE} taken LOW after \overline{CAS} goes LOW result in a LATE WRITE (\overline{OE} -controlled) cycle.
15. Output parameter (I/O) is referenced to corresponding \overline{CAS} input, I/O0-I/O7 by \overline{LCAS} and I/O8-I/O15 by \overline{UCAS} .
16. During a READ cycle, if \overline{OE} is LOW then taken HIGH before \overline{CAS} goes HIGH, I/O goes open. If \overline{OE} is tied permanently LOW, a LATE WRITE or READ-MODIFY-WRITE is not possible.
17. Write command is defined as \overline{WE} going low.
18. LATE WRITE and READ-MODIFY-WRITE cycles must have both t_{OD} and t_{OEH} met (\overline{OE} HIGH during WRITE cycle) in order to ensure that the output buffers will be open during the WRITE cycle. The I/Os will provide the previously written data if \overline{CAS} remains LOW and \overline{OE} is taken back to LOW after t_{OEH} is met.
19. The I/Os are in open during READ cycles once t_{OD} or t_{OFF} occur.
20. The first $\chi\overline{CAS}$ edge to transition LOW.
21. The last $\chi\overline{CAS}$ edge to transition HIGH.
22. These parameters are referenced to \overline{CAS} leading edge in EARLY WRITE cycles and \overline{WE} leading edge in LATE WRITE or READ-MODIFY-WRITE cycles.
23. Last falling $\chi\overline{CAS}$ edge to first rising $\chi\overline{CAS}$ edge.
24. Last rising $\chi\overline{CAS}$ edge to next cycle's last rising $\chi\overline{CAS}$ edge.
25. Last rising $\chi\overline{CAS}$ edge to first falling $\chi\overline{CAS}$ edge.
26. Each $\chi\overline{CAS}$ must meet minimum pulse width.
27. Last $\chi\overline{CAS}$ to go LOW.
28. I/Os controlled, regardless \overline{UCAS} and \overline{LCAS} .
29. The 3 ns minimum is a parameter guaranteed by design.
30. Enables on-chip refresh and address counters.

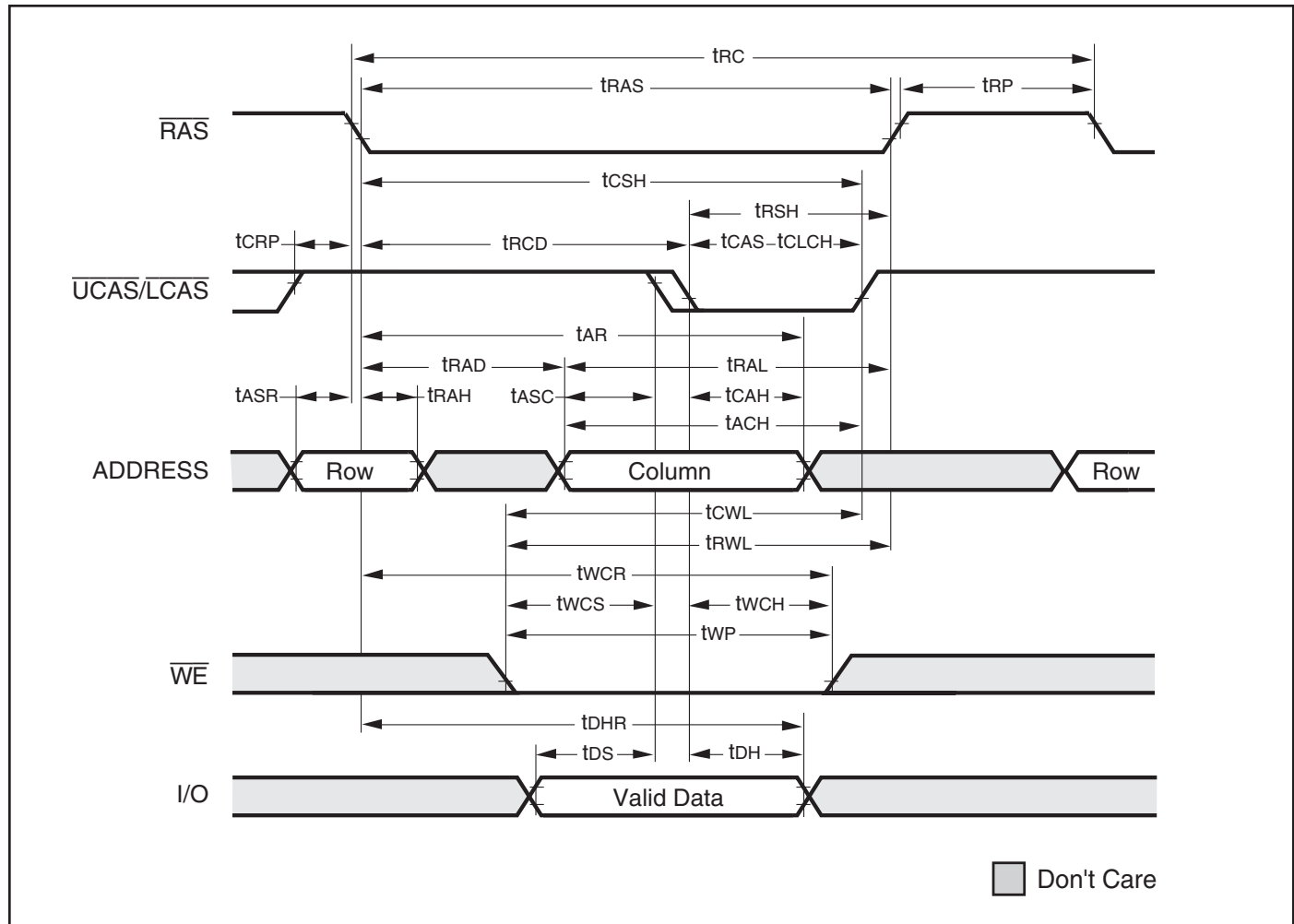
READ CYCLE



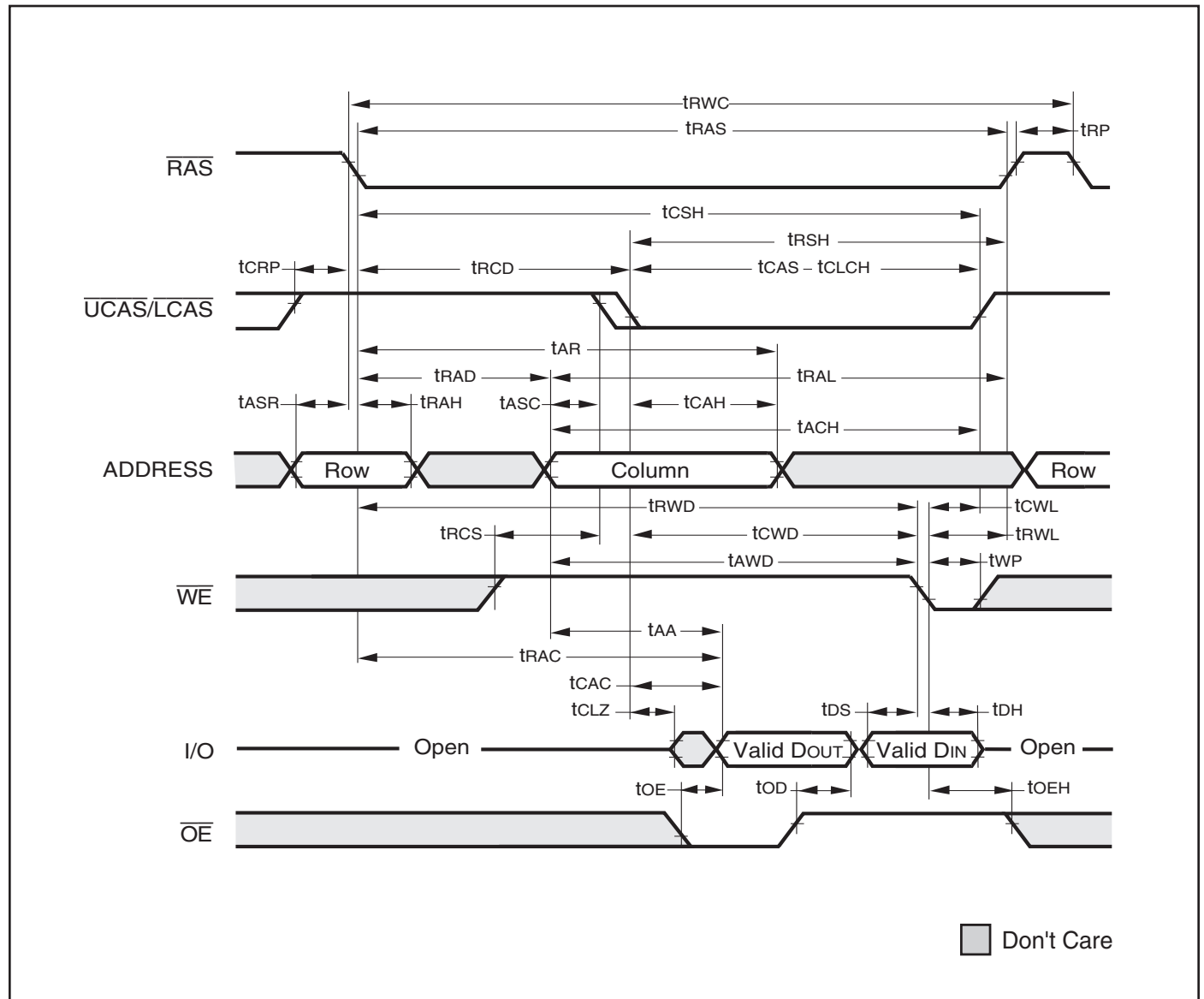
Note:

1. t_{OFF} is referenced from rising edge of \overline{RAS} or \overline{CAS} , whichever occurs last.

EARLY WRITE CYCLE (\overline{OE} = DON'T CARE)

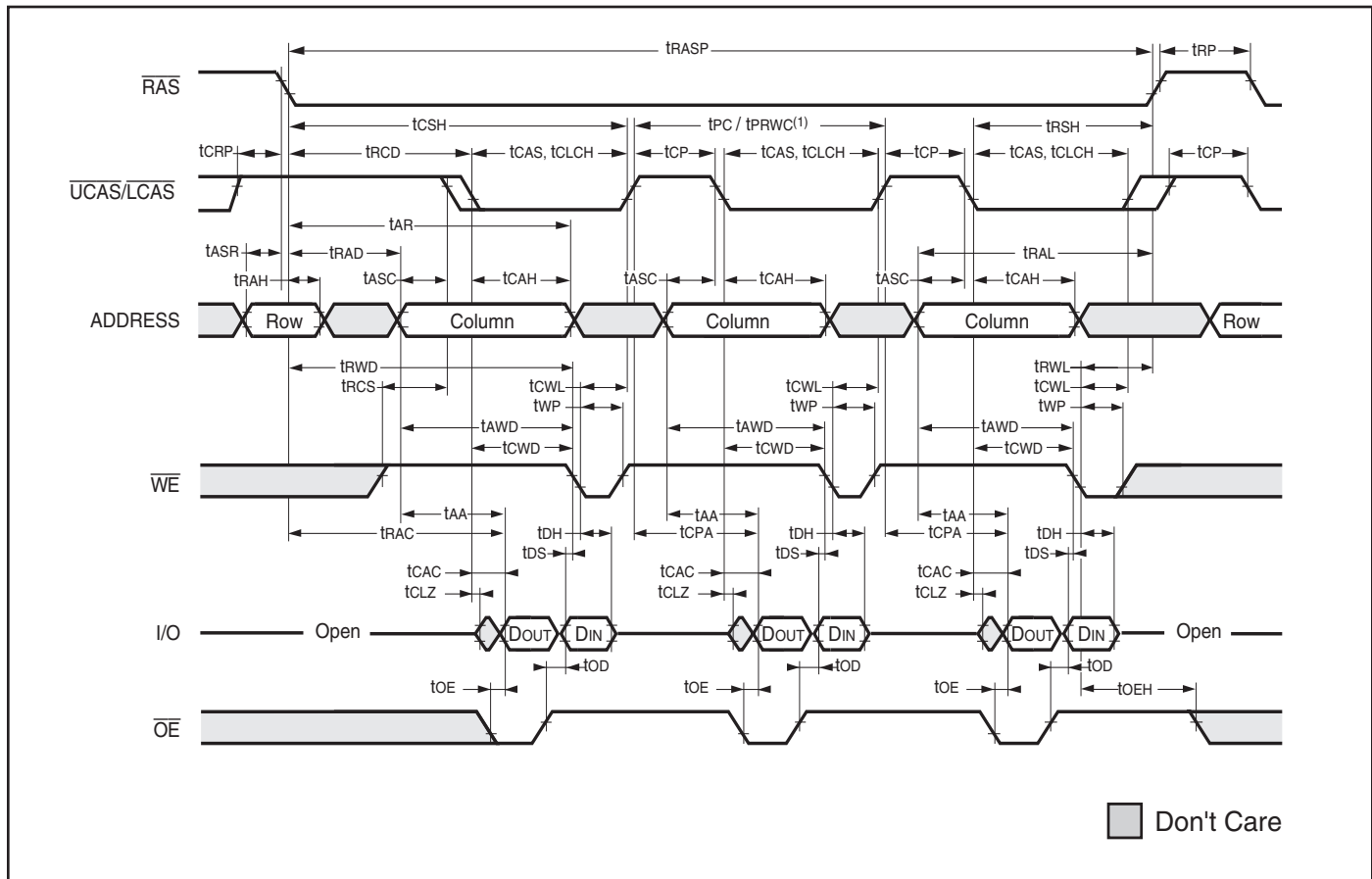


READ WRITE CYCLE (LATE WRITE and READ-MODIFY-WRITE Cycles)



Integrated Silicon Solution, Inc.
Rev. A
1/31/2013

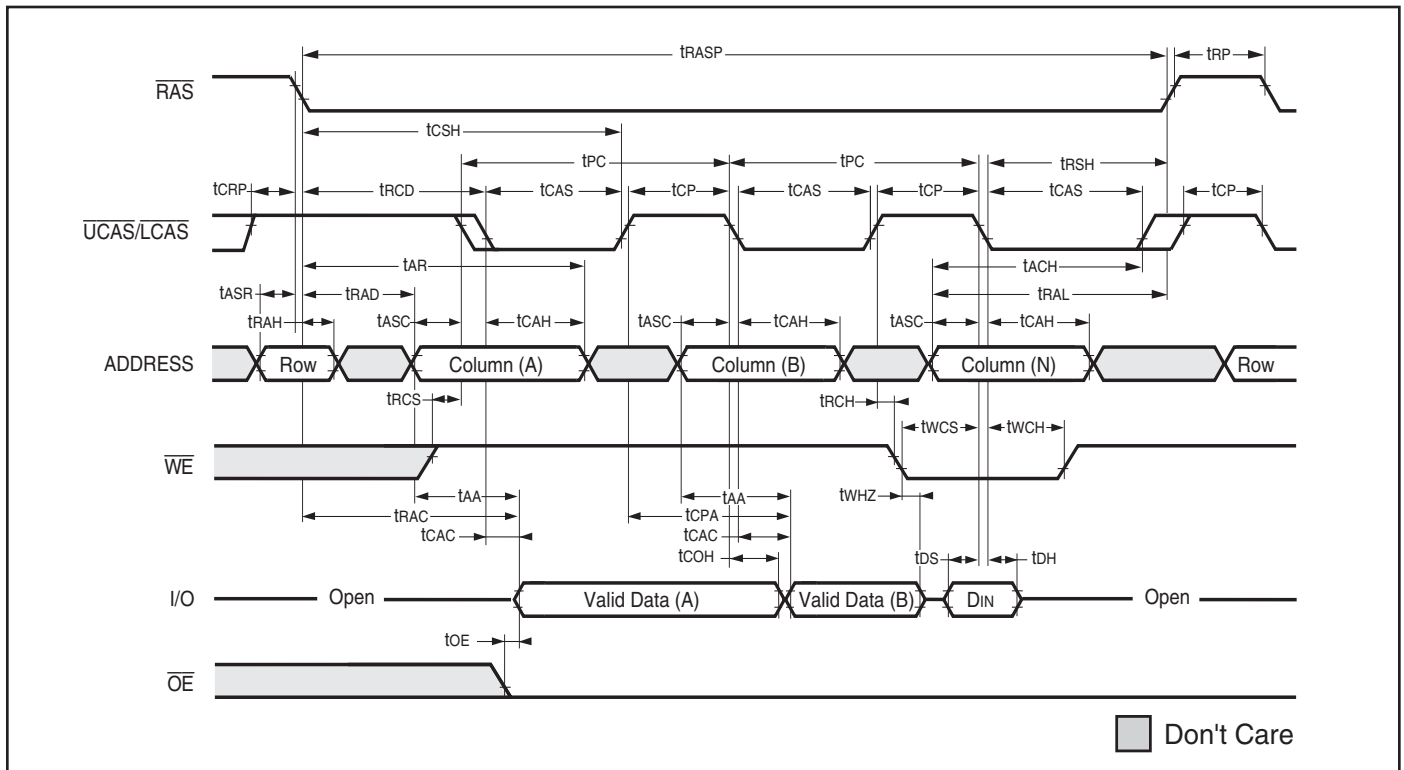
EDO-PAGE-MODE READ-WRITE CYCLE (LATE WRITE and READ-MODIFY WRITE Cycles)



Note:

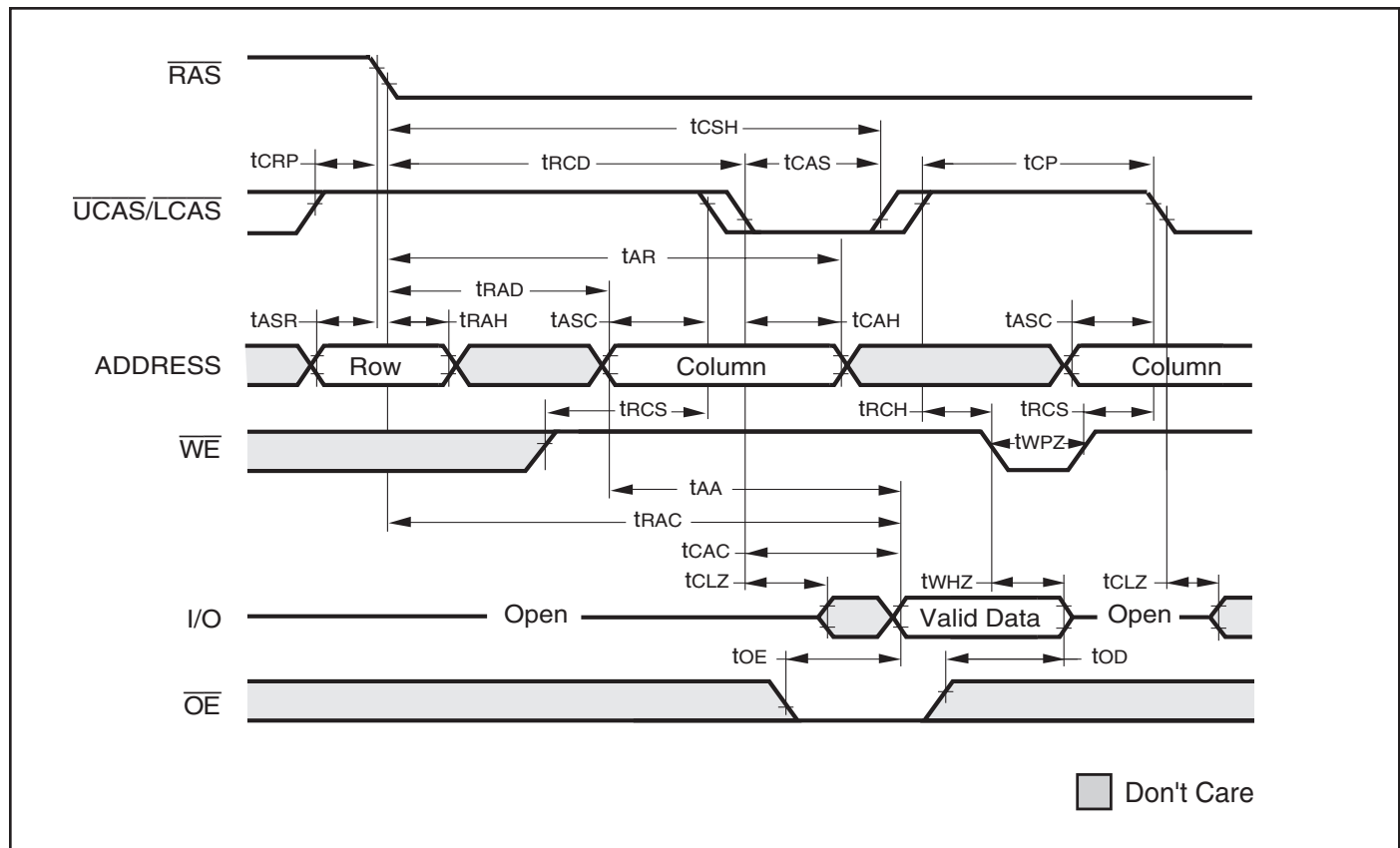
1. t_{PC} can be measured from falling edge of \overline{CAS} to falling edge of \overline{CAS} , or from rising edge of \overline{CAS} to rising edge of \overline{CAS} . Both measurements must meet the t_{PC} specifications.

EDO-PAGE-MODE READ-EARLY-WRITE CYCLE (Pseudo READ-MODIFY WRITE)

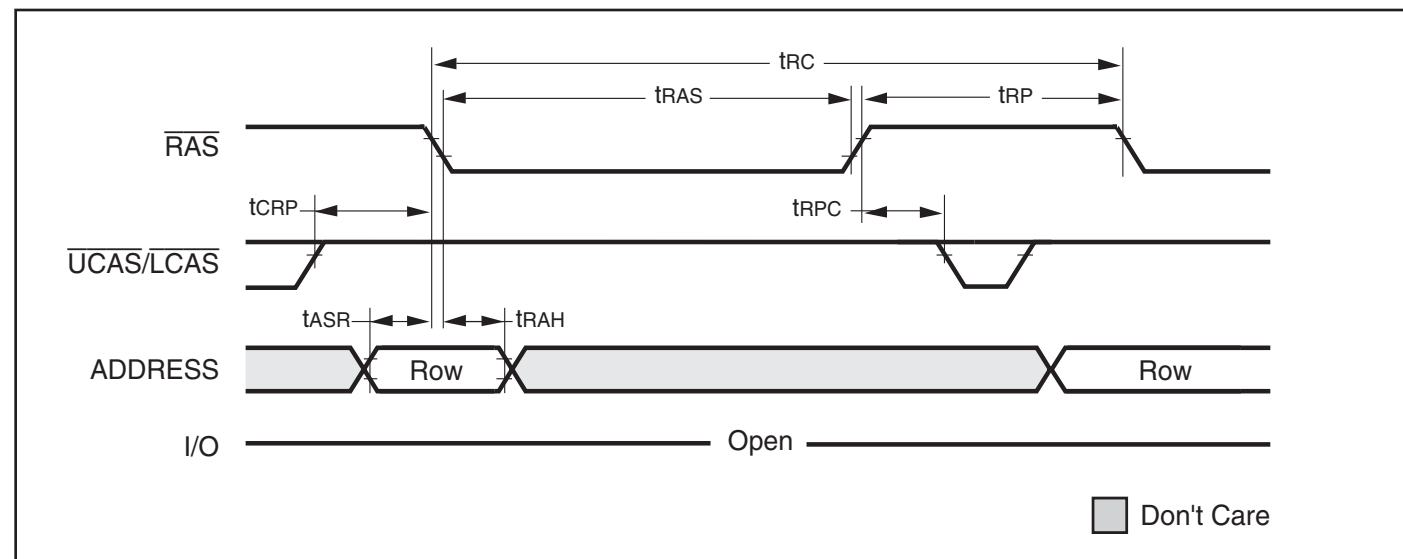


AC WAVEFORMS

READ CYCLE (With \overline{WE} -Controlled Disable)



\overline{RAS} -ONLY REFRESH CYCLE (\overline{OE} , \overline{WE} = DON'T CARE)



The diagram illustrates the timing relationships for a 2D DRAM array. The signals and their timing parameters are as follows:

- RAS:** Row Address Strobe. Timing parameters include t_{RAS} (pulse width), t_{RP} (period from RAS to next RAS), and t_{CRP} (time from RAS to UCAS/LCAS).
- UCAS/LCAS:** Column Address Strobe/Latch Enable. Timing parameters include t_{RCD} (time from RAS to UCAS/LCAS), t_{TRSH} (time from UCAS/LCAS to RAS), and t_{CHR} (time from UCAS/LCAS to RAS).
- ADDRESS:** The address bus, divided into Row and Column phases. Timing parameters include t_{ASR} (time from RAS to Row address), t_{RAD} (time from RAS to Row address), t_{AR} (time from Row address to RAS), t_{RAH} (time from Row address to RAS), t_{ASC} (time from Row address to Column address), t_{AL} (time from Column address to RAS), t_{CAH} (time from Column address to RAS), t_{AA} (time from Row address to Column address), t_{RAC} (time from Row address to Column address), t_{CLZ} (time from Column address to RAS), t_{CAC} (time from Column address to RAS), and $t_{TOFF(2)}$ (time from RAS to Column address).
- I/O:** Data bus. Timing parameters include t_{OE} (time from RAS to I/O), t_{ORD} (time from RAS to I/O), t_{OD} (time from RAS to I/O), and $t_{OFF(2)}$ (time from RAS to I/O).
- OE:** Output Enable. Timing parameters include t_{OE} (time from RAS to OE), t_{ORD} (time from RAS to OE), and t_{OD} (time from RAS to OE).

Legend: Don't Care

19

ORDERING INFORMATION : 3.3V

Industrial Range: -40°C to +85°C

| Speed (ns) | Order Part No. | Package |
|------------|--------------------|-----------------------------------|
| 35 | IS41LV16256C-35TI | 400-mil TSOP (Type II) |
| | IS41LV16256C-35TLI | 400-mil TSOP (Type II), Lead-free |

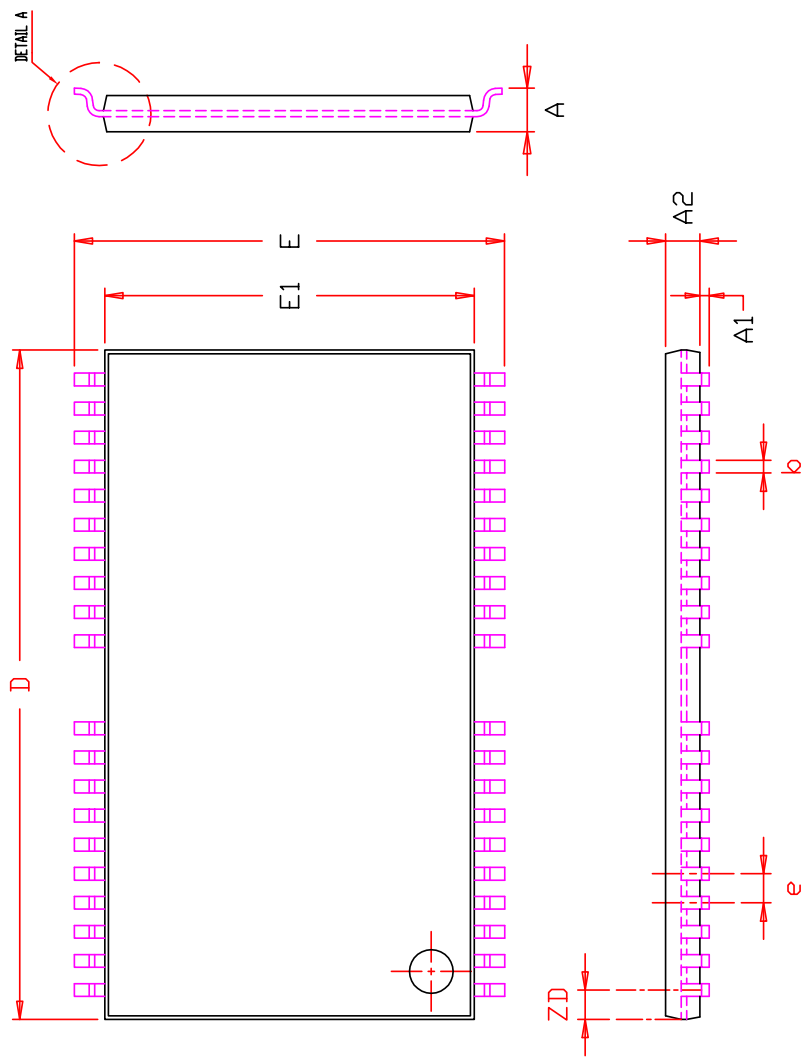
ORDERING INFORMATION : 5V

Industrial Range: -40°C to +85°C

| Speed (ns) | Order Part No. | Package |
|------------|-------------------|-----------------------------------|
| 35 | IS41C16256C-35TI | 400-mil TSOP (Type II) |
| | IS41C16256C-35TLI | 400-mil TSOP (Type II), Lead-free |

Note:

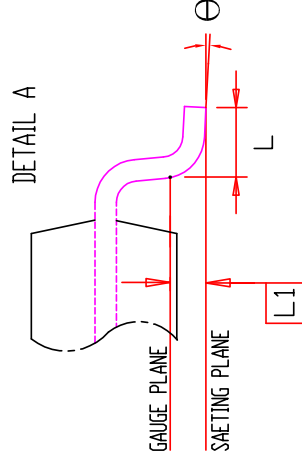
The -35 speed option supports 35ns and 60ns timing specifications.



| SYMBOL | DIMENSION IN MM | | | DIMENSION IN INCH | | |
|--------|-----------------|-------|-------|-------------------|-------|-------|
| | MIN. | NOM. | MAX. | MIN. | NOM. | MAX. |
| A | 1.00 | | 1.20 | 0.039 | | 0.047 |
| A1 | 0.05 | | 0.15 | 0.002 | | 0.006 |
| A2 | 0.95 | 1.00 | 1.05 | 0.037 | 0.039 | 0.041 |
| b | 0.30 | | 0.45 | 0.012 | | 0.018 |
| D | 18.28 | 18.41 | 18.54 | 0.720 | 0.725 | 0.730 |
| E | 11.56 | 11.76 | 11.96 | 0.455 | 0.463 | 0.471 |
| E1 | 10.03 | 10.16 | 10.29 | 0.395 | 0.400 | 0.405 |
| e | 0.80 | BSC. | 0.031 | BSC. | | |
| L | 0.40 | | 0.69 | 0.016 | | 0.027 |
| L1 | 0.25 | BSC. | 0.010 | BSC. | | |
| ZD | 0.805 | REF. | 0.032 | REF. | | |
| θ | 0 | | 8° | 0 | | 8° |

NOTE :

1. CONTROLLING DIMENSION : MM
2. DIMENSION D AND E1 DO NOT INCLUDE MOLD PROTRUSION.
3. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION/INTRUSION.



| | | | | | | |
|------|-------|---|------|---|------|------------|
| ISSI | TITLE | 40/44L 400mil TSOP-2 Package Outline | REV. | F | DATE | 03/19/2009 |
|------|-------|---|------|---|------|------------|



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



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